

# MMBD352LT1G, MMBD353LT1G, NSVMMBD353LT1G, MMBD354LT1G, NSVMMBD354LT1G, MMBD355LT1G



ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)

## Dual Hot Carrier Mixer Diodes

These devices are designed primarily for UHF mixer applications but are suitable also for use in detector and ultra-fast switching circuits.

### Features

- Very Low Capacitance – Less Than 1.0 pF @ Zero V
- Low Forward Voltage – 0.5 V (Typ) @  $I_F = 10$  mA
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS (EACH DIODE)

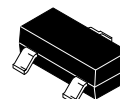
Rating	Symbol	Value	Unit
Continuous Reverse Voltage	$V_R$	7.0	$V_{CC}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

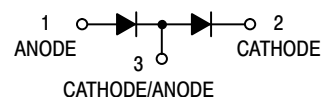
### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

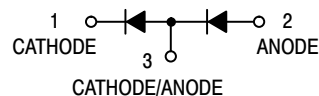
1. FR-5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



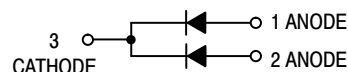
SOT-23 (TO-236)  
CASE 318



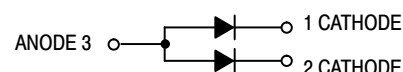
MMBD352LT1G  
STYLE 11



MMBD353LT1G  
NSVMMBD353LT1G  
STYLE 19

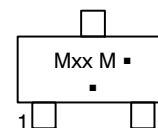


MMBD354LT1G  
NSVMMBD354LT1G  
STYLE 9



MMBD355LT1G  
STYLE 12

### MARKING DIAGRAM



Mxx = Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)  
\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

### ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

# MMBD352LT1G, MMBD353LT1G, NSVMMBD353LT1G, MMBD354LT1G, NSVMMBD354LT1G, MMBD355LT1G

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted) (EACH DIODE)

Rating	Symbol	Min	Max	Unit
Forward Voltage ( $I_F = 10 \text{ mA}_{dc}$ )	$V_F$	-	0.60	V
Reverse Leakage Current (Note 3) ( $V_R = 3.0 \text{ V}$ ) ( $V_R = 7.0 \text{ V}$ )	$I_R$	- -	0.25 10	$\mu\text{A}$
Capacitance ( $V_R = 0 \text{ V}$ , $f = 1.0 \text{ MHz}$ )	C	-	1.0	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

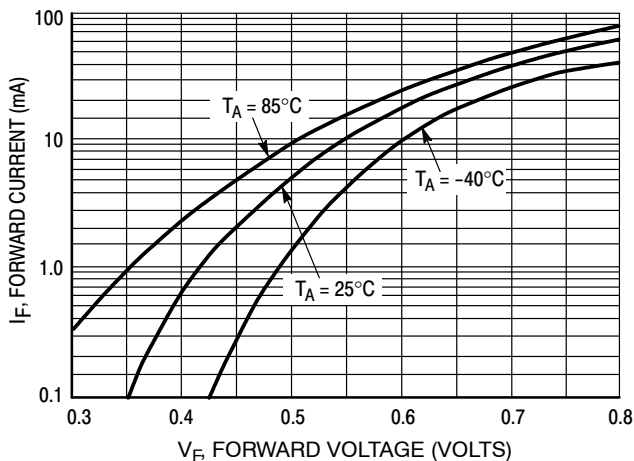
3. For each individual diode while the second diode is unbiased.

## ORDERING INFORMATION

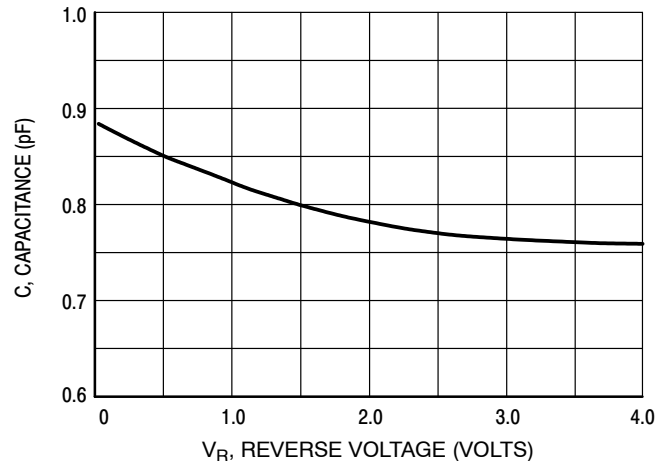
Device	Marking	Package	Shipping <sup>†</sup>
MMBD352LT1G	M5G	SOT-23 (Pb-Free)	3,000 Units / Tape & Reel
MMBD352LT3G	M5G	SOT-23 (Pb-Free)	10,000 Units / Tape & Reel
MMBD353LT1G	M4F	SOT-23 (Pb-Free)	3,000 Units / Tape & Reel
NSVMMBD353LT1G	M4F	SOT-23 (Pb-Free)	3,000 Units / Tape & Reel
MMBD353LT3G	M4F	SOT-23 (Pb-Free)	10,000 Units / Tape & Reel
MMBD354LT1G	M6H	SOT-23 (Pb-Free)	3,000 Units / Tape & Reel
NSVMMBD354LT1G	M6H	SOT-23 (Pb-Free)	3,000 Units / Tape & Reel
MMBD355LT1G	MJ1	SOT-23 (Pb-Free)	3,000 Units / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## TYPICAL CHARACTERISTICS



**Figure 1. Forward Voltage**

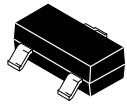


**Figure 2. Capacitance**

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



**SOT-23 (TO-236)**  
**CASE 318-08**  
**ISSUE AS**

DATE 30 JAN 2018

SCALE 4:1

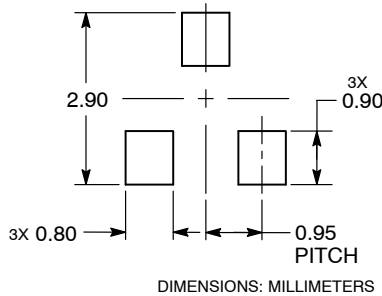


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**RECOMMENDED SOLDERING FOOTPRINT**



**GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

- |                                                             |                                                             |                                                             |                                                            |
|-------------------------------------------------------------|-------------------------------------------------------------|-------------------------------------------------------------|------------------------------------------------------------|
| STYLE 1 THRU 5:<br>CANCELLED                                | STYLE 6:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR       | STYLE 7:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR       | STYLE 8:<br>PIN 1. ANODE<br>2. NO CONNECTION<br>3. CATHODE |
| STYLE 9:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE          | STYLE 10:<br>PIN 1. DRAIN<br>2. SOURCE<br>3. GATE           | STYLE 11:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE-ANODE | STYLE 12:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE      |
| STYLE 13:<br>PIN 1. SOURCE<br>2. DRAIN<br>3. GATE           | STYLE 14:<br>PIN 1. CATHODE<br>2. GATE<br>3. ANODE          | STYLE 15:<br>PIN 1. GATE<br>2. CATHODE<br>3. ANODE          | STYLE 16:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE      |
| STYLE 17:<br>PIN 1. NO CONNECTION<br>2. ANODE<br>3. CATHODE | STYLE 18:<br>PIN 1. NO CONNECTION<br>2. CATHODE<br>3. ANODE | STYLE 19:<br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE-ANODE | STYLE 20:<br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE         |
| STYLE 21:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN           | STYLE 22:<br>PIN 1. RETURN<br>2. OUTPUT<br>3. INPUT         | STYLE 23:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE         | STYLE 24:<br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE          |
| STYLE 25:<br>PIN 1. ANODE<br>2. CATHODE<br>3. GATE          | STYLE 26:<br>PIN 1. CATHODE<br>2. ANODE<br>3. NO CONNECTION | STYLE 27:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE     | STYLE 28:<br>PIN 1. ANODE<br>2. ANODE<br>3. ANODE          |

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<b>DESCRIPTION:</b>	<b>SOT-23 (TO-236)</b>	<b>PAGE 1 OF 1</b>

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